## 1. General description

NPN high-voltage low  $V_{CEsat}$  in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9115Z

### 2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- Medium power SMD plastic package

## 3. Applications

- LED driver for LED chain module
- LCD backlighting
- · High Intensity Discharge (HID) front lighting
- · Automotive motor management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	150	V
I <sub>C</sub>	collector current		-	-	1	Α
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C	100	250	-	



### 150 V, 1 A NPN high-voltage low VCEsat transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	С
2	С	collector		
3	Е	emitter		B —
4	С	collector	<u>∃</u> 1 <u>∃</u> 2 <u>∃</u> 3	Ė
			SC-73 (SOT223)	sym123

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package						
	Name	Description	Version				
PBHV8115Z		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223				

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBHV8115Z	V8115Z

#### 150 V, 1 A NPN high-voltage low VCEsat transistor

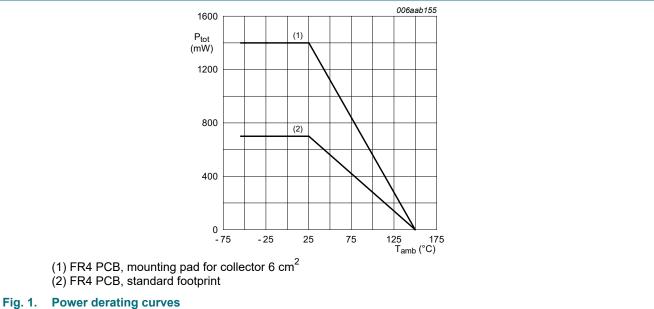
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	400	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	150	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	2	Α
I <sub>BM</sub>	peak base current			-	400	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.7	W
			[2]	-	1.4	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



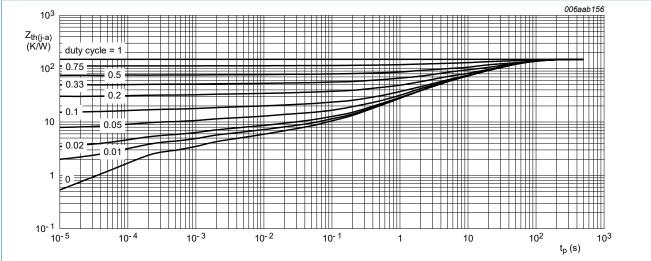
#### 150 V, 1 A NPN high-voltage low VCEsat transistor

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

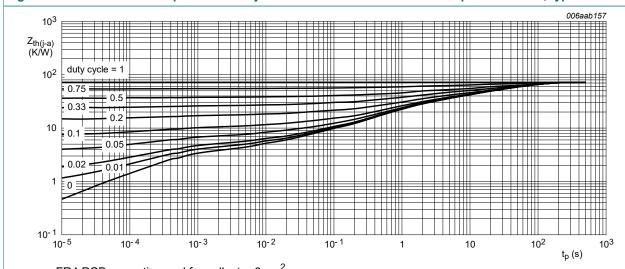
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	-	175	K/W
juncti	unction to ambient		[2]	-	-	89	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 150 V, 1 A NPN high-voltage low VCEsat transistor

## 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	10	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 120 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C	100	250	-	
		V <sub>CE</sub> = 10 V; I <sub>C</sub> = 100 mA; T <sub>amb</sub> = 25 °C	100	250	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	50	160	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 1 A; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	10	30	-	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 10 mA; T <sub>amb</sub> = 25 °C	-	40	60	mV
	saturation voltage	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 20 mA; T <sub>amb</sub> = 25 °C	-	33	50	mV
		$I_C$ = 1 A; $I_B$ = 200 mA; pulsed; $t_p \le$	-	225	350	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	1.1	1.2	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 6 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 0.1 A;	-	7	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	-	565	-	ns
t <sub>on</sub>	turn-on time		-	572	-	ns
t <sub>s</sub>	storage time		-	1530	-	ns
t <sub>f</sub>	fall time		-	700	-	ns
t <sub>off</sub>	turn-off time		-	2230	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	30	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	5.7	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	150	-	pF

#### 150 V, 1 A NPN high-voltage low VCEsat transistor

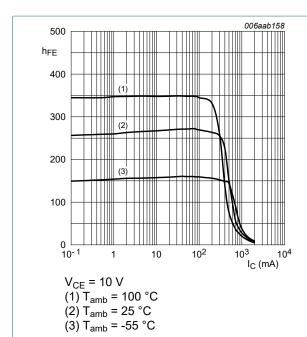


Fig. 4. DC current gain as a function of collector current; typical values

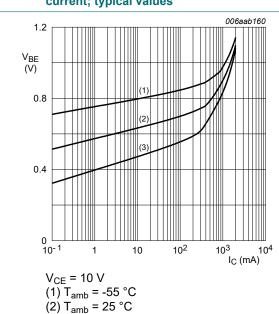


Fig. 6. Base-emitter voltage as a function of collector current; typical values

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

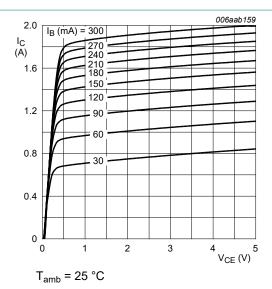
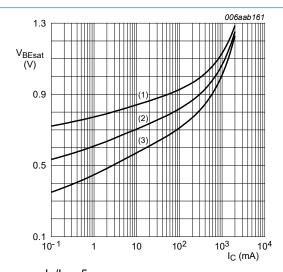


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $I_{C}/I_{B} = 5$ (1)  $T_{amb} = -55 \,^{\circ}C$ (2)  $T_{amb} = 25 \,^{\circ}C$ 

(3) T<sub>amb</sub> = 100 °C

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

#### 150 V, 1 A NPN high-voltage low VCEsat transistor

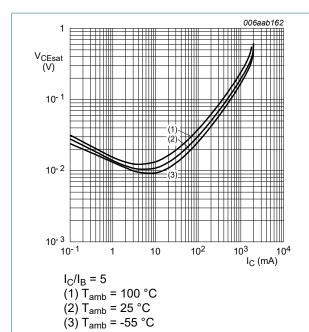


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

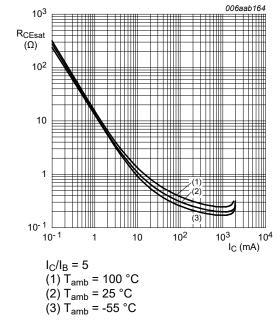


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

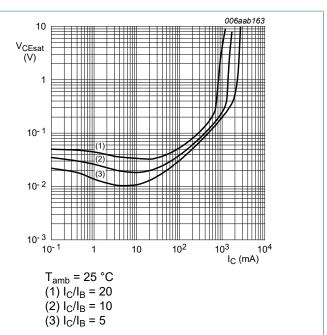


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

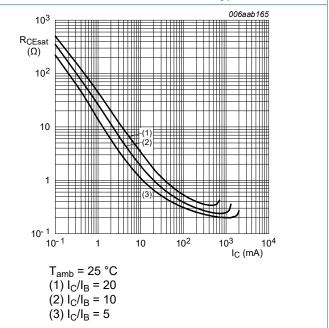
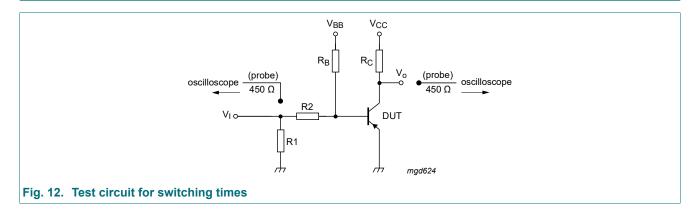


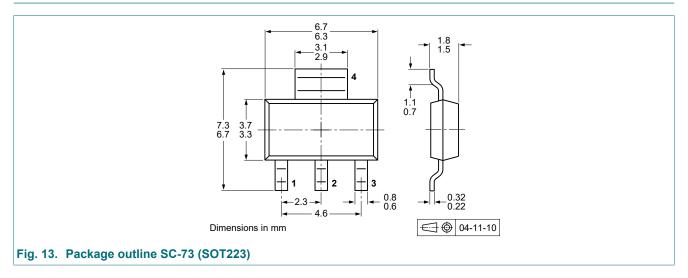
Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

### 150 V, 1 A NPN high-voltage low VCEsat transistor

## 11. Test information

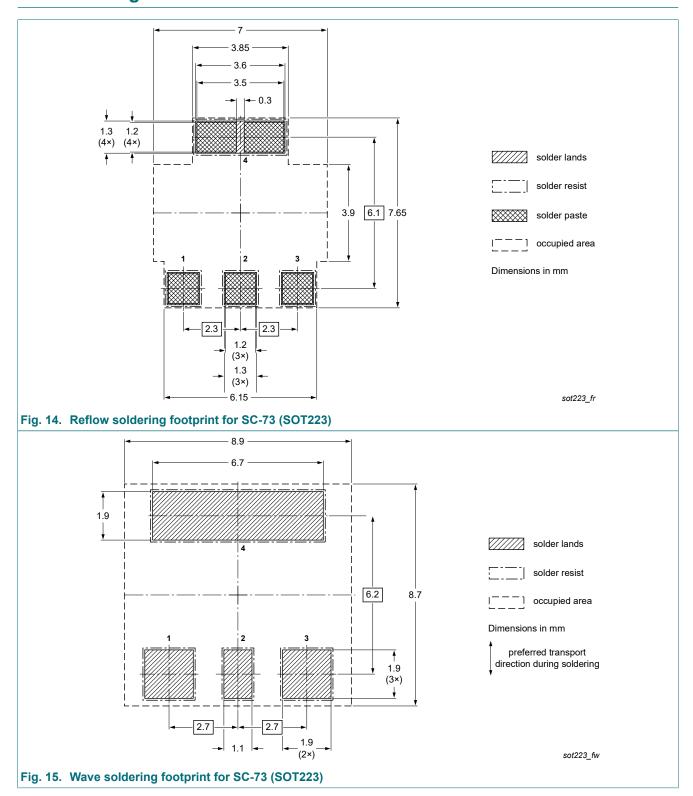


## 12. Package outline



### 150 V, 1 A NPN high-voltage low VCEsat transistor

## 13. Soldering



### 150 V, 1 A NPN high-voltage low VCEsat transistor

# 14. Revision history

### **Table 8. Revision history**

Table 6. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBHV8115Z v.4	20241008	Product data sheet	-	PBHV8115Z v.3			
Modifications:		Product(s) changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s).					
PBHV8115Z v.3	20230721	Product data sheet	-	PBHV8115Z_2			
PBHV8115Z_2	20081209	Product data sheet	-	PBHV8115Z_1			
PBHV8115Z_1	20080205	Product data sheet	-	-			

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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